

# PMDPB55XP

# 20 V, dual P-channel Trench MOSFET Rev. 3 — 4 June 2012

Product data sheet

#### 1. **Product profile**

## 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless ultra thin DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction

## 1.3 Applications

- Charging switch for portable devices
- DC/DC converters
- Small brushless DC motor drive
- Power management in battery-driven portables
- Hard disc and computing power management

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-	-4.5	Α
Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3.4 \text{ A}; T_j = 25 \text{ °C}$		-	55	70	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2 _   _
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	G1 S1 S2 G2
7	D1	drain TR1	Transparent top view	017aaa258
8	D2	drain TR2	SOT1118 (DFN2020-6)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMDPB55XP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118			

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PMDPB55XP	1Z

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	r					
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-4.5	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-3.4	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	-2.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	490	mW
			<u>[1]</u>	-	1170	mW
		T <sub>sp</sub> = 25 °C		-	8300	mW
Source-drain	diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-1.2	Α
Per device						
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

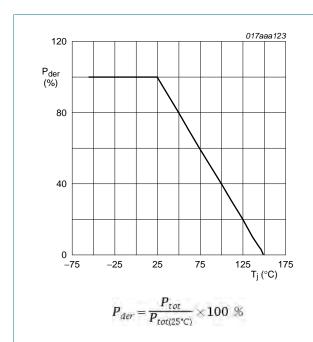
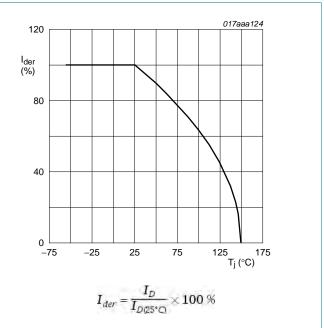
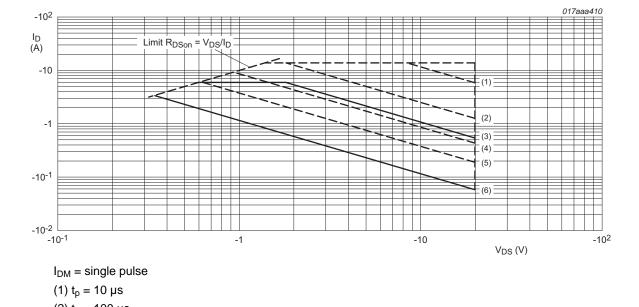


Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature



- (2)  $t_p = 100 \mu s$
- (3) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (4)  $t_p = 10 \text{ ms}$
- $(5) t_p = 100 ms$
- (6) DC; T<sub>amb</sub> = 25 °C; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
Per transistor R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	223	256	K/W
			[2]	-	93	107	K/W
		in free air; t ≤ 5 s	[2]	-	55	63	K/W
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point	in free air		-	10	15	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

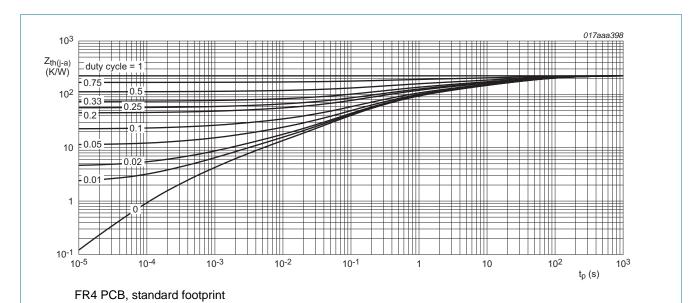


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

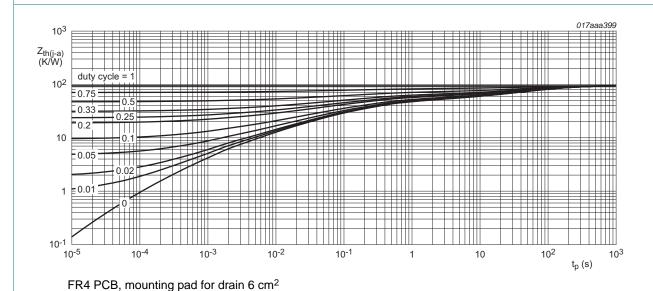


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.47	-0.65	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -3.4 \text{ A}; T_j = 25 \text{ °C}$	-	55	70	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3.4 \text{ A}; T_j = 150 \text{ °C}$	-	78	99	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1.6 \text{ A}; T_j = 25 \text{ °C}$	-	75	90	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.5 \text{ A}; T_j = 25 \text{ °C}$	-	110	135	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -3.4 \text{ A}; T_j = 25 \text{ °C}$	-	15	-	S
Dynamic	characteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -3.4 \text{ A}; V_{GS} = -5 \text{ V};$	-	16.5	25	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
$Q_{GD}$	gate-drain charge		-	1.65	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	785	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	80	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	64	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -3.4 \text{ A}; V_{GS} = -5 \text{ V};$	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	135	-	ns
t <sub>f</sub>	fall time		-	68	-	ns
Source-d	rain diode (per transistor)					
$V_{SD}$	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.8	-1.2	V

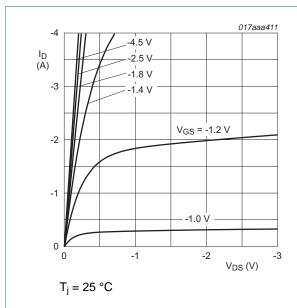


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

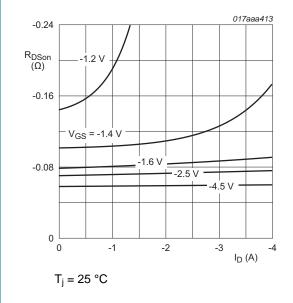
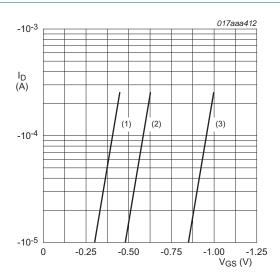


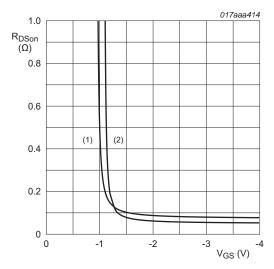
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, \text{V}$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

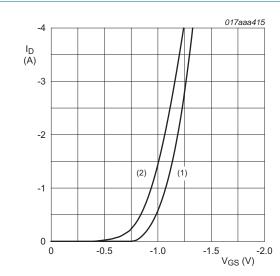


 $I_{D} = -1 A$ 

(1) 
$$T_i = 150 \, ^{\circ}C$$

(2)  $T_j = 25 \,{}^{\circ}\text{C}$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

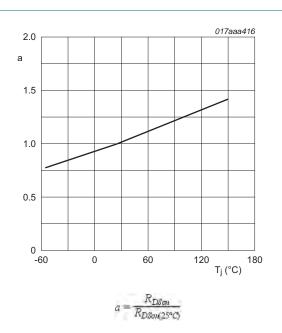
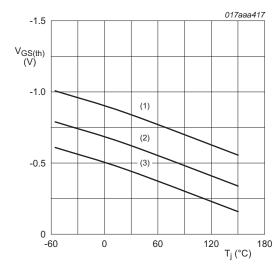


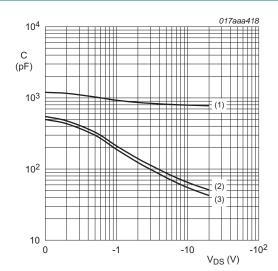
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

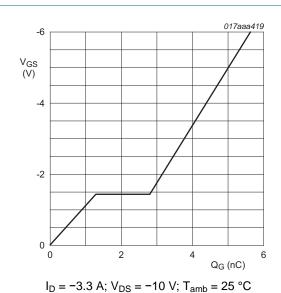
Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V<sub>GS</sub>(pl)

V<sub>GS</sub>(th)

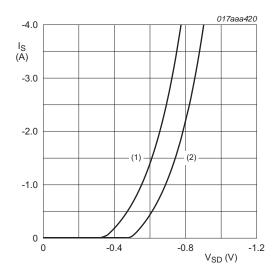
V<sub>GS</sub>

Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>G</sub>(tot)

017aaa137

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



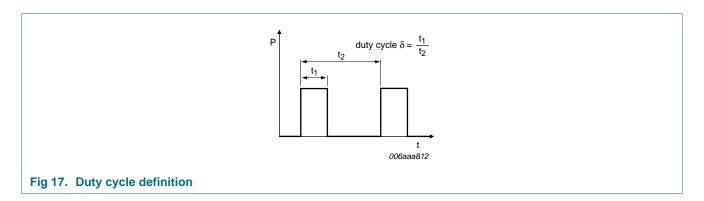
 $V_{GS} = 0 V$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ 

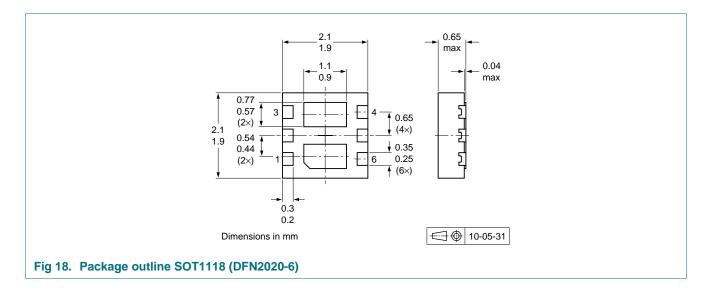
(2)  $T_{amb} = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

# 8. Test information



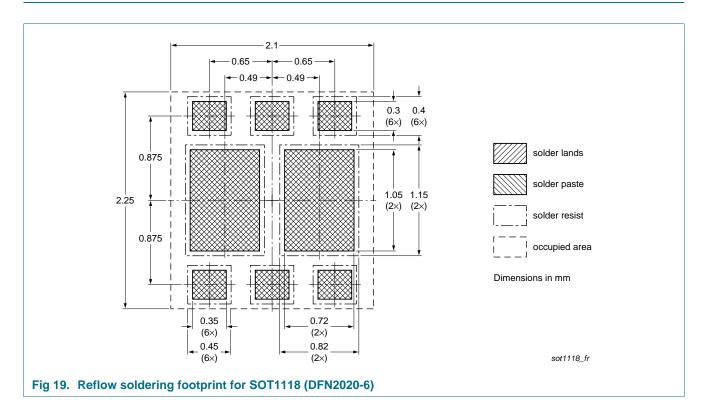
# 9. Package outline



PMDPB55XP

20 V, dual P-channel Trench MOSFET

# 10. Soldering



# 11. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB55XP v.3	20120604	Product data sheet	-	PMDPB55XP v.2
Modifications:	• Table 7.: V <sub>GSth</sub>	values updated		
PMDPB55XP v.2	20120502	Product data sheet	-	PMDPB55XP v.1
PMDPB55XP v.1	20120309	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions".
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PMDPB55XP

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Nexperia PMDPB55XP

#### 20 V, dual P-channel Trench MOSFET

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# **Nexperia**

# PMDPB55XP

20 V, dual P-channel Trench MOSFET

# 14. Contents

1	Product profile	.1
1.1	General description	.1
1.2	Features and benefits	.1
1.3	Applications	.1
1.4	Quick reference data	.1
2	Pinning information	.2
3	Ordering information	.2
4	Marking	
5	Limiting values	.3
6	Thermal characteristics	.4
7	Characteristics	.6
8	Test information	10
9	Package outline	10
10	Soldering	11
11	Revision history	12
12	Legal information	13
12.1	Data sheet status	13
12.2	Definitions	13
12.3	Disclaimers	13
12.4	Trademarks	14
12	Contact information	11